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ULTRA-LOW-NOISE TRANSIMPEDANCE AMPLIFIER FOR HIGH-PERFORMANCE MEMS RESONANT GYROSCOPES

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Motivation

- The performance of MEMS gyroscopes is rapidly approaching the level that can be adopted in a wide range of military and high-end industrial applications.
- One of the most highly desired applications for a high-performance gyroscope is GPS-free inertial navigation for autonomous cars, drones, and indoor pedestrians and it is required to have very high bias stability (< 0.1 deg/hr)

Objective

- Implementation of a front-end capacitive readout circuitry with extremely low noise, wide dynamic range, and high tolerance to variations in voltage and temperature to overcome the performance limits of existing gyroscopes.
- Implementation of a front-end capacitive readout circuitry with a wide feedback control range to detect a wide range of capacitances and frequencies

Challenges of Front-End Circuitry

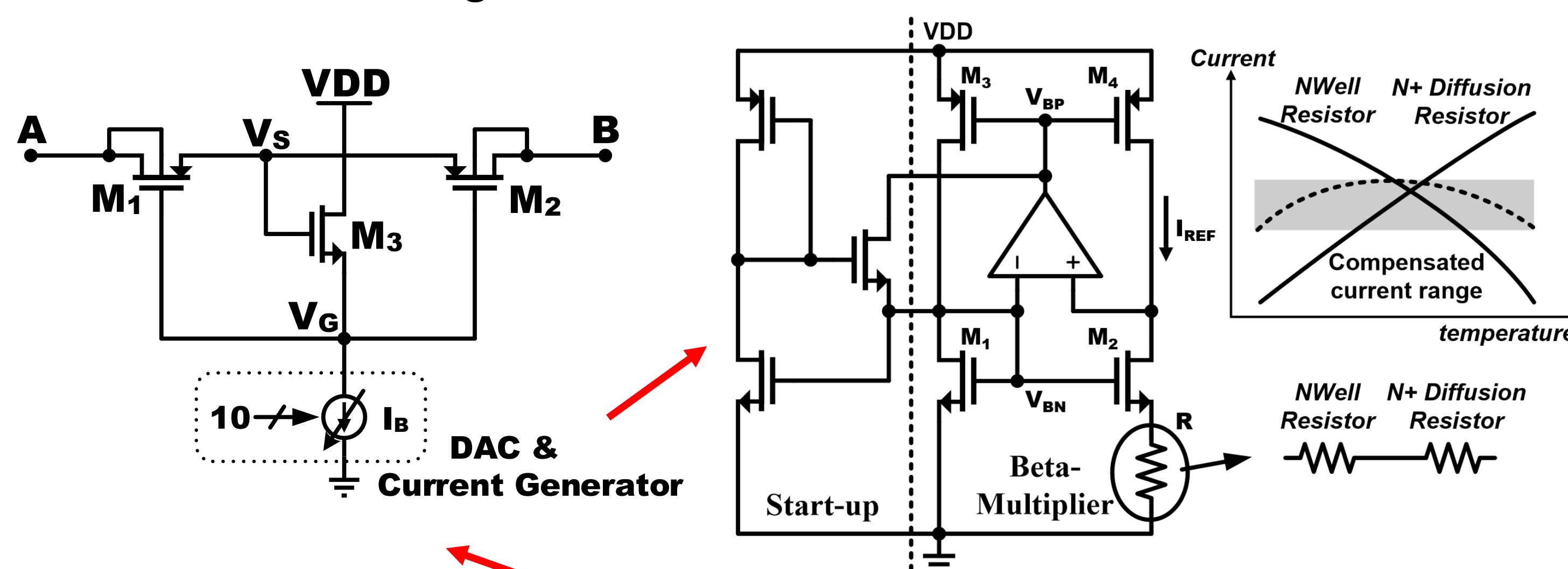
- Large output swing to cover a wide range of sensitivity
- Low distortion to get the high linearity
- Large and controllable feedback gain to cover a wide range of capacitances
- Easy on-chip integration to reduce parasitic

Trans-impedance Amplifier for Front-End

- Relatively insensitive to parasitic
- Easy control of feedback gain
- Two-chip cost effective solution
- Proof-mass not switched

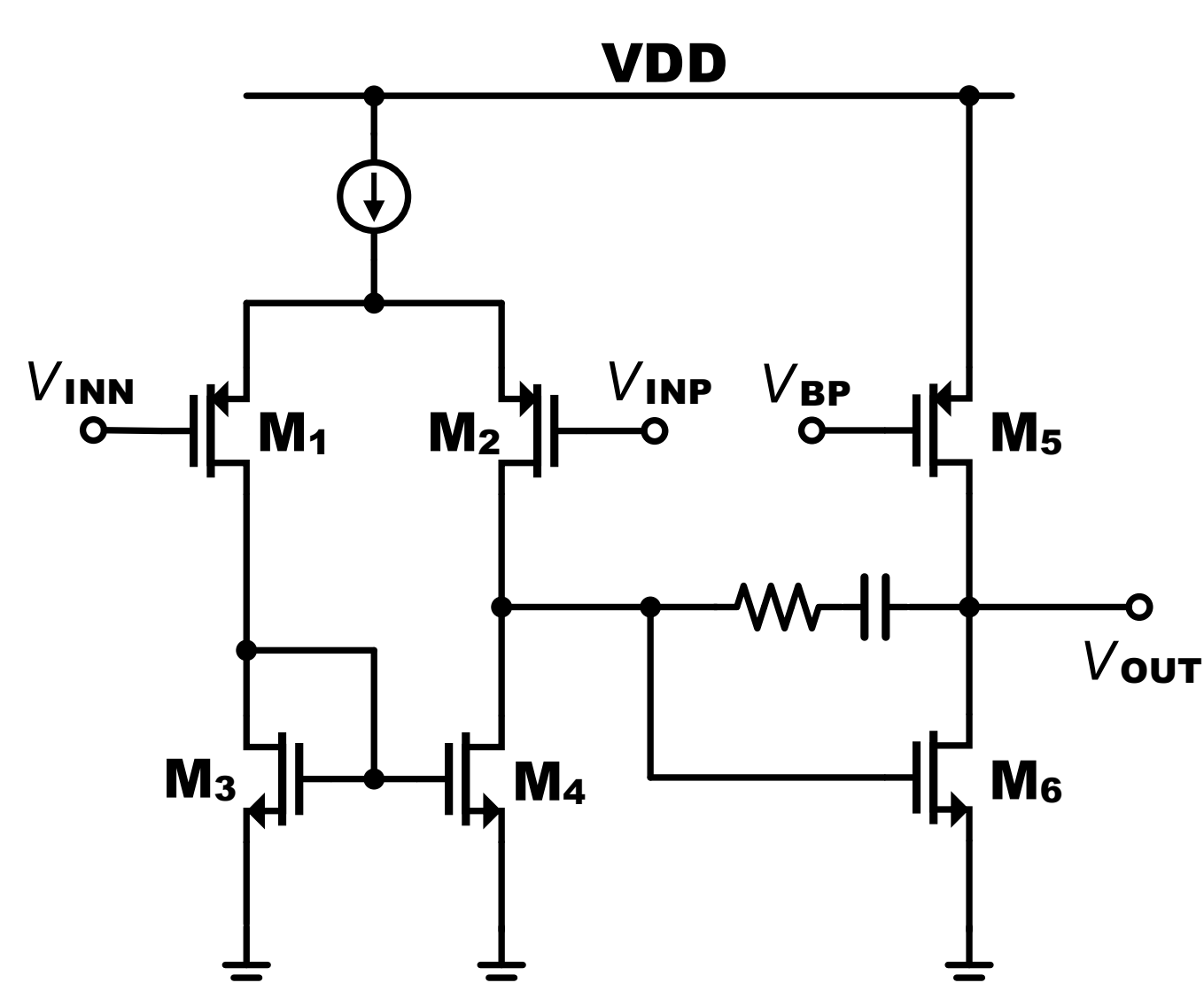
Entire Circuit Implementation

- Variable Floating Resistor with 10-b Current Steering DAC
- Voltage-Temperature tolerant Current Generator



- TIA with Floating Resistor T-Network
 - Covers wide range of readout capacitances and frequency ranges
 - Compensates for process and temperature variations
 - Reduces TIA noise by the integrated resistance control block

- Low-noise Two Stage Amplifier



$$\overline{V_{n,thermal}^2} \approx \frac{16kT}{3} \frac{1}{g_{m1}^2} (g_{m1} + g_{m3})$$

$$\overline{V_{n,flicker}^2} \approx \frac{2}{C_{ox}f} \left(\frac{K_p}{W_1 L_1} + \frac{\mu_n K_n L_1}{\mu_p W_1 L_3^2} \right)$$

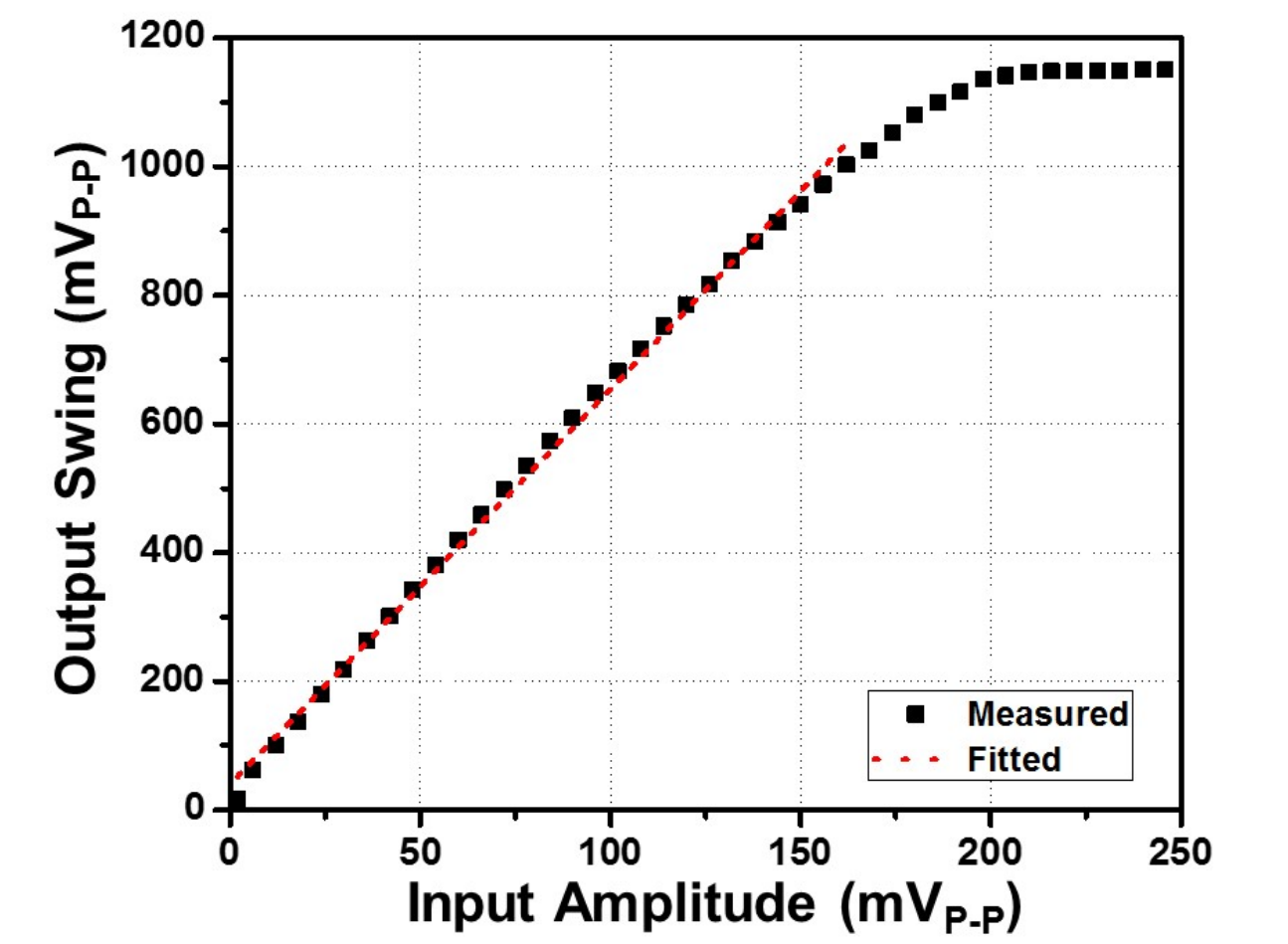
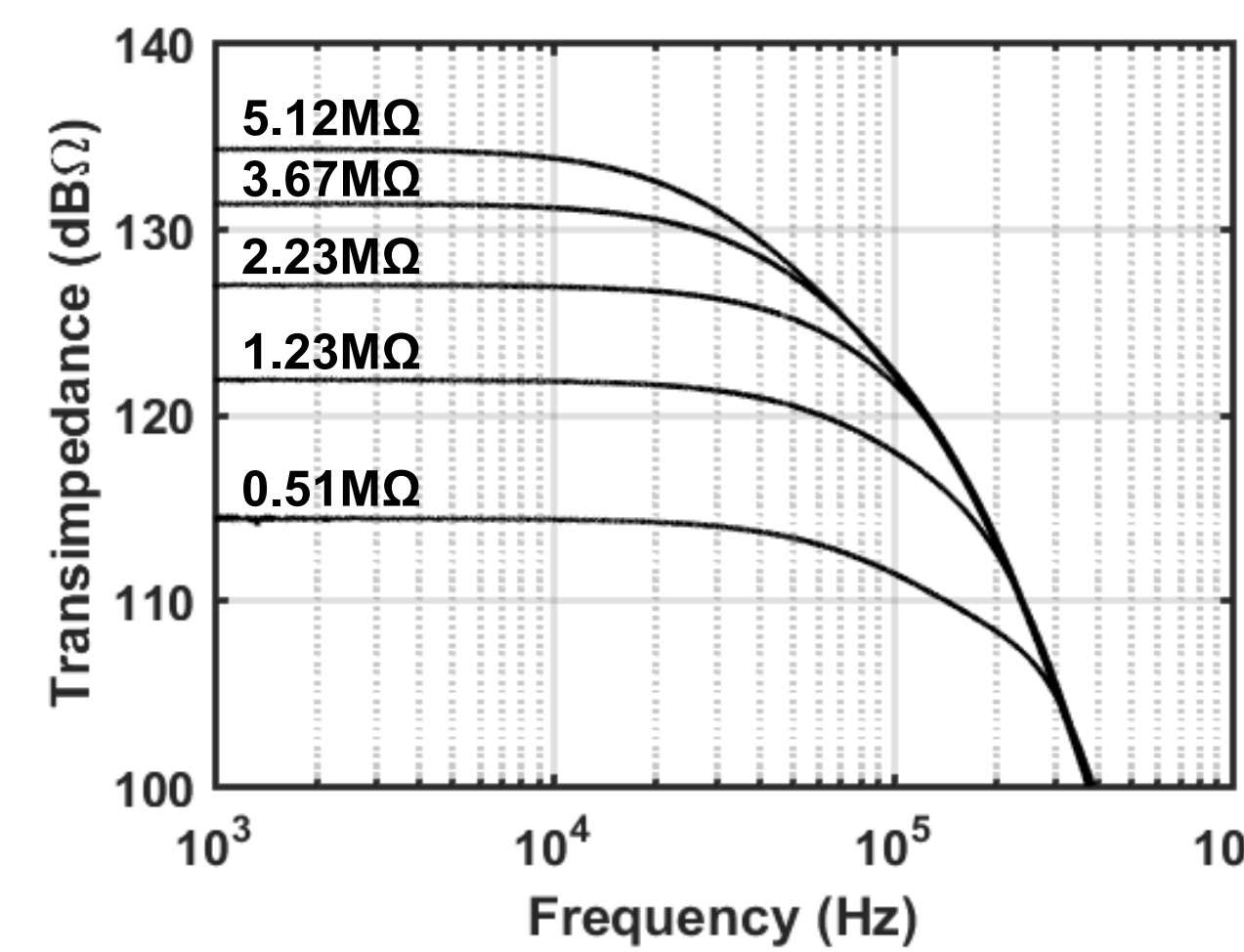
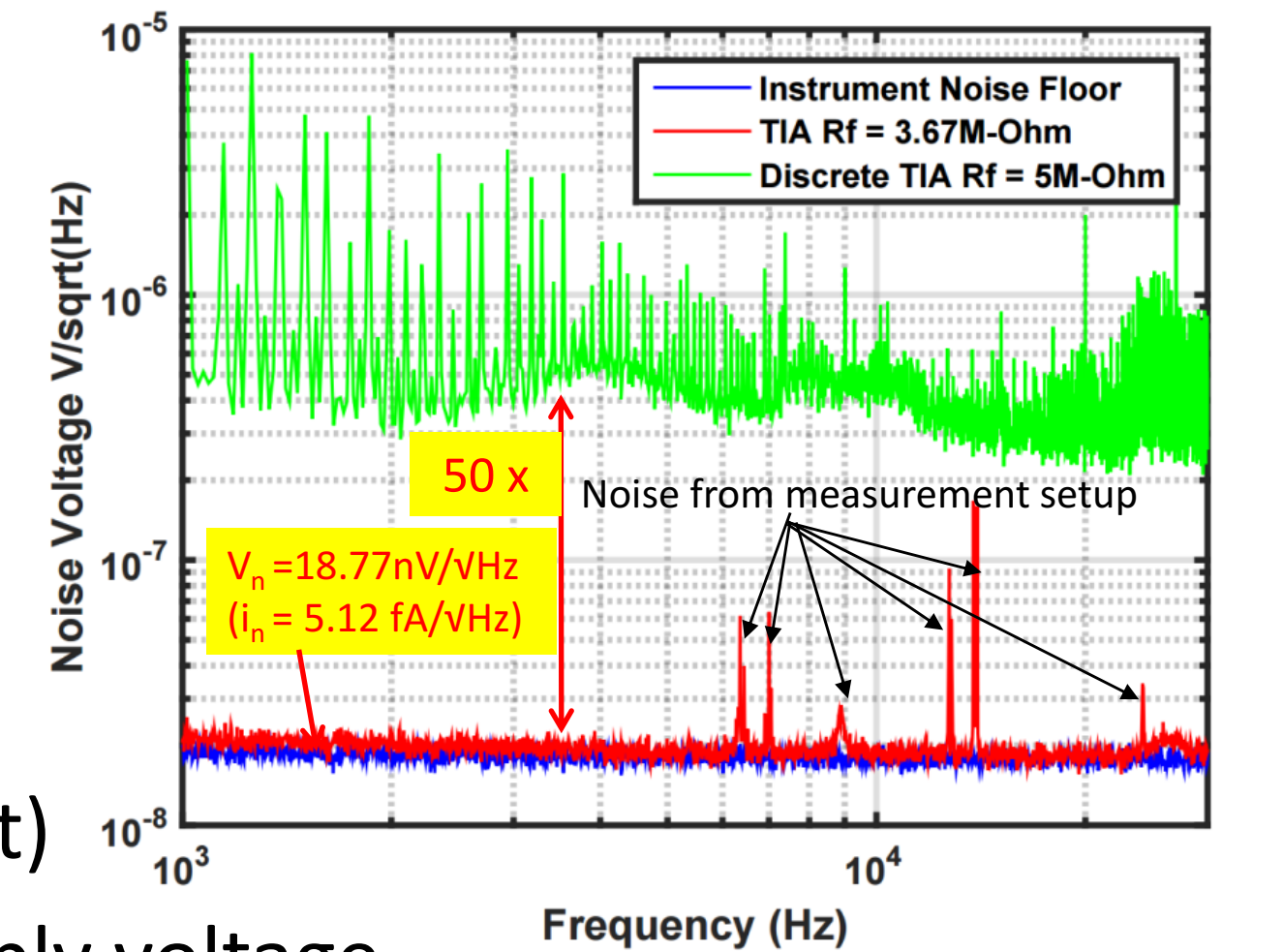
- $W_1 \uparrow$
 - $g_{m1} \uparrow$
 - Thermal noise \downarrow
 - Flicker noise \downarrow
- $L_3 \uparrow$
 - Sig. swing \downarrow
 - Flicker noise \downarrow

Accomplishments

- Implemented a new TIA that employs an on-chip digitally-controlled floating resistor as the variable resistor for a resistor T-network to lower the noise and obtain higher linearity .
- Measured very low input current noise ($i_n=5.12\text{fA}/\text{VHz}$) which translates to 0.45 zF/VHz minimum detectable capacitance and very wide dynamic range (123 dB).
- Demonstrated near-navigation-grade bias instability (0.0391 deg/hr).

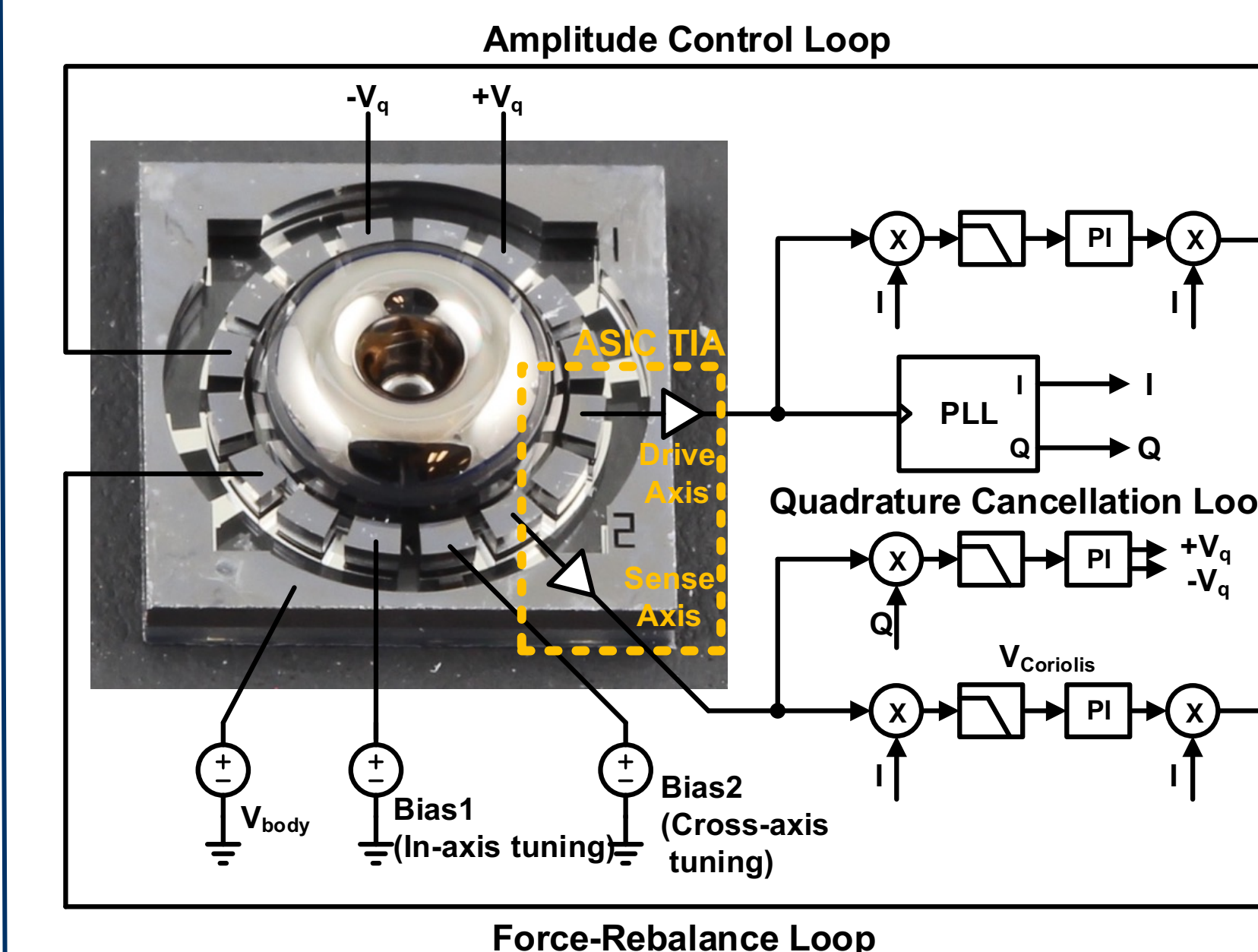
Evaluation of Proposed CMOS TIA

- Comparison between output noise spectral densities of TIA ASIC and discrete low-noise TIA (Right)
 - ~50 times lower noise floor
- Measured T-network TIA gain (Lower Left)
 - Wide and controllable feedback gain
- Measured T-network TIA gain (Lower Right)
 - Large output swing even with low supply voltage



Performance Summary and Comparison Results

| | |
|------------------------------|-------------------------------|
| Technology | 0.18 μm 1P6M CMOS |
| Feedback Gain Range | 510k Ω -5.12M Ω |
| Output swing | Up to 955mV _{p-p} |
| Input referred current noise | 5.12 fA/VHz (@10KHz) |
| Min. detectable capacitance | 0.45 zF/VHz |
| Dynamic Range | 123dB |



| | |
|-----------------------|---|
| Resonator Dimension | Radius (R): 2.5 mm Height (H): 1.55 mm |
| Frequency ($f_n=2$) | 9030.925 Hz 9030.998 Hz |
| Quality Factor | 419.047k (14.77s) 410.176k (14.14s) |
| Scale Factor | 100 mV/deg/s |
| Bias Stability | 0.0391 deg/h |

| References | J.A. Geen et al. | A. Sharma et al. | L. Aaltonen et al. | This work |
|----------------------------------|------------------|------------------|--------------------|-----------|
| Front-End Architecture | CSA* | TIA | CSA* | TIA |
| Input Current Noise (fA/VHz) | - | 88 | - | 5.12 |
| Minimum Detectable Cap. (zF/VHz) | 12 (zF) | 20** | 220 | 0.45*** |
| Bias instability (deg/h) | 50 | 0.16 | 25 | 0.0391 |

*: Charge sense amplifier **: $V_{Bias}=40\text{V}$, $f=15\text{kHz}$ ***: $V_{Bias}=200\text{V}$, $f=9.03\text{kHz}$

Summary and Future Work

- Demonstrated the fully integrated CMOS TIA with one-of-the lowest reported noise performance and very wide dynamic range.
- Demonstrated the rate-mode operation of FS μ -BRG with one-of-the-best performance among existing MEMS gyroscopes.
- Will implement a miniaturized system with low-noise and high performance.

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